## **RSC Advances**



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## CORRECTION



Cite this: RSC Adv., 2017, 7, 10557

## Correction: The polarization-dependent anisotropic Raman response of few-layer and bulk WTe<sub>2</sub> under different excitation wavelengths

Qingjun Song,<sup>ab</sup> Haifeng Wang,<sup>cd</sup> Xiaolong Xu,<sup>ab</sup> Xingchen Pan,<sup>cd</sup> Yilun Wang,<sup>ab</sup> Fengqi Song,<sup>cd</sup> Xiangang Wan<sup>\*cd</sup> and Lun Dai<sup>\*ab</sup>

DOI: 10.1039/c7ra90007d

www.rsc.org/advances

Correction for 'The polarization-dependent anisotropic Raman response of few-layer and bulk WTe<sub>2</sub> under different excitation wavelengths' by Qingjun Song *et al.*, *RSC Adv.*, 2016, **6**, 103830–103837.

In part (d) of Fig. 4 of the original manuscript, and in the description of part (d) in the Fig. 4 caption, the wrong labels were given for the modes. The labels "B<sub>g</sub>" and "A<sub>u</sub>" should be "B<sub>u</sub>" and "A<sub>g</sub>", respectively. The corrected Fig. 4 and its caption are shown below: Additionally, in the Results and Discussion section, in the text below Fig. 4, two sentences should be revised as follows:

"For  $E_{\text{las}} \approx 2.3$  eV, the excited electron will transit from the A<sub>g</sub> valence band to A<sub>u</sub> conductance band, and the corresponding polar plot is shown in Fig. 4(e), where the maximum (minimum) absorption corresponds to the perpendicular (parallel) relation between the incident polarization and *a*-axis".

"To study the influence of electron-photon interaction on the anisotropic Raman scattering, we first assume the electron-phonon interaction  $(H_{e-ph})$  in the Raman scattering is not polarization dependent".

<sup>e</sup>State Key Lab for Mesoscopic Physics, School of Physics, Peking University, Beijing 100871, China. E-mail: lundai@pku.edu.cn <sup>b</sup>Collaborative Innovation Center of Quantum Matter, Beijing 100871, China <sup>c</sup>National Laboratory of Solid State Microstructures, College of Physics, Nanjing University, Nanjing 210093, China. E-mail: xgwan@nju.edu.cn <sup>d</sup>Collaborative Innovation Center of Advanced Microstructures, Nanjing University, Nanjing 210093, China



Fig. 4 (a-c) The calculated band structures of monolayer, bilayer and bulk WTe<sub>2</sub>, respectively. The representative band symmetries at  $\Gamma$  point are labelled, and the insets are their 2D Brillouin zones. Calculated polarization dependence of the optical transition probability (d) from the B<sub>u</sub> to A<sub>a</sub>  $(E_{las} \approx 1.5 \text{ eV})$  and (e) from the A<sub>g</sub> to A<sub>u</sub> ( $E_{las} \approx 2.3 \text{ eV}$ ) in monolayer WTe<sub>2</sub>, as indicated in (a). 0° corresponds to the W–W chain (a-axis) direction, the initial incident polarization and scattered polarization are along the *a*-axis ( $\theta_0 = 0^\circ$ ). (f) The representative calculated polarization dependent intensities of  $A_q$  and  $B_q$  modes in monolayer WTe<sub>2</sub> with certain  $\theta_0$  (~15°).

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.